

**SEMICONDUCTOR
TECHNICAL DATA**

KTD1898

EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION.

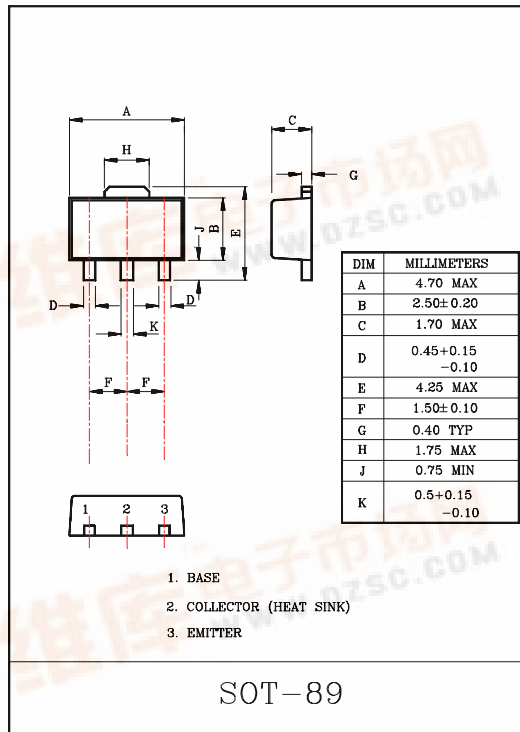
FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTB1260.

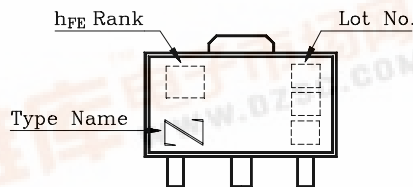
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	1	A
Emitter Current	I _E	-1	A
Collector Power Dissipation	P _C	500	mW
	P _{C*}	1	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

P_{C*} : KTD1898 mounted on ceramic substrate (250mm²x0.8t)



Marking



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} =80V, I _E =0	-	-	1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =4V, I _C =0	-	-	1	μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	80	-	-	V
DC Current Gain	h _{FE} (Note)	V _{CE} =3V, I _C =500mA	70	-	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =500mA, I _B =20mA	-	-	0.4	V
Transition Frequency	f _T	V _{CE} =10V, I _E =-50mA, f=100MHz	-	100	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	20	-	pF

Note : h_{FE} Classification O:70~140 , Y:120~240 , GR : 200~400

